BF370 TRANSISTOR (NPN)

TO-92

1.EMITTER
2.COLLECTOR
3.BASE

FEATURES

- Low Saturation Medium Current Application
- High Transition Frequency

ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
BF370	TO-92	Bulk	1000pcs/Bag
BF370-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	15	V
V_{EBO}	Emitter-Base Voltage	4.5	V
I_C	Collector Current	0.1	A
P_C	Collector Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	250	℃/W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

T_a=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= 0.1mA,I_E=0	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	15			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA,I_C=0	4.5			V
Collector cut-off current	I_{CBO}	V_{CB}=20V,I_E=0			0.4	μA
Emitter cut-off current	I_{EBO}	V_{EB}=2V,I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}=1V, I_C=10mA	40		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=15mA,I_B=1.5mA			0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=15mA,I_B=1.5mA			1.2	V
Transition frequency	f_T	V_{CE}=10V,I_C= 10mA,f=100 MHz	500			MHz